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Kind regards,

Team Nexperia



PMBTA44

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

Rev. 01 — 22 February 2008 Product data s

Product data sheet

Product profile

1.1 General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low current (max. 300 mA)
- High voltage (max. 400 V)
- AEC-Q101 qualified

1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	400	V
I _C	collector current		-	-	300	mA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}$	50	-	200	



400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2. Pinning

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Pin	Description	Simplified outline	Symbol
1	base		
2	emitter	<u> 3</u>	3
3	collector	1 2	1 —
			svm021

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBTA44	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMBTA44	W3*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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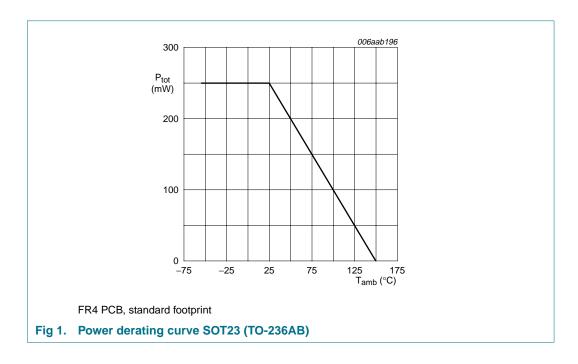
400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	500	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	300	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	300	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		–55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

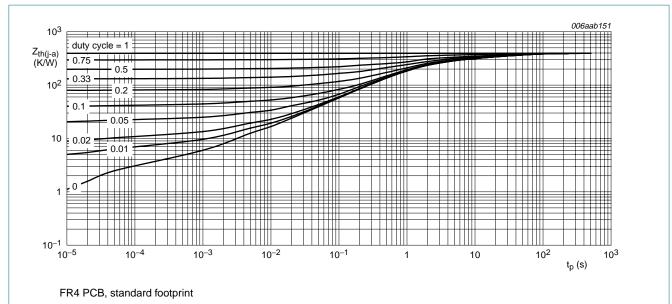


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB)

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

7. Characteristics

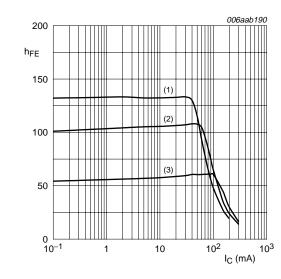
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

amb							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 320 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nΑ
	current	$V_{CB} = 320 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$		-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_C = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V					
		I _C = 10 mA		50	-	200	
		$I_C = 50 \text{ mA}$	<u>[1]</u>	45	-	-	
		I _C = 100 mA	<u>[1]</u>	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 1 \text{ mA}; I_B = 0.1 \text{ mA}$		-	-	400	mV
		$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$		-	-	500	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	[1]	-	-	750	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	[1]	-	-	850	mV
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_E = 10 \text{ mA};$ f = 100 MHz		20	-	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V; } I_E = i_e = 0 \text{ A;}$ f = 1 MHz		-	-	7	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$		-	-	180	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

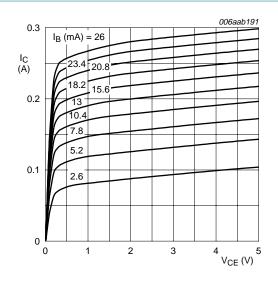
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$$V_{CE} = 10 \text{ V}$$

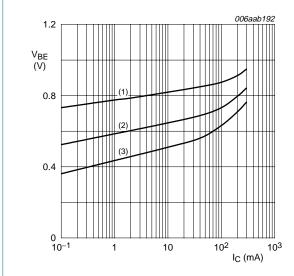
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

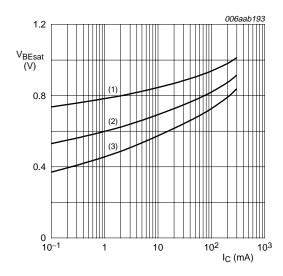
Fig 4. Collector current as a function of collector-emitter voltage; typical values



V_{CE} = 10 V

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

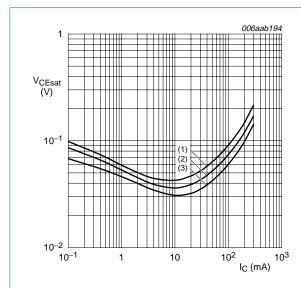


 $I_{\rm C}/I_{\rm B}=5$

- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

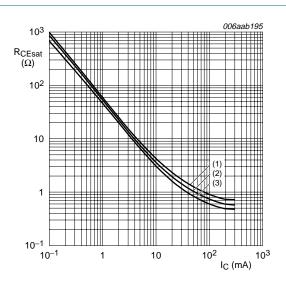
400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor



$$I_{\rm C}/I_{\rm B}=5$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=5$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Collector-emitter saturation resistance as a function of collector current; typical values

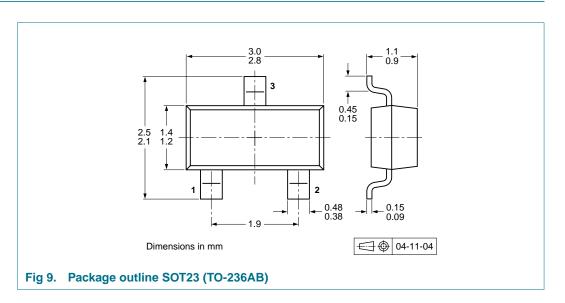
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8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

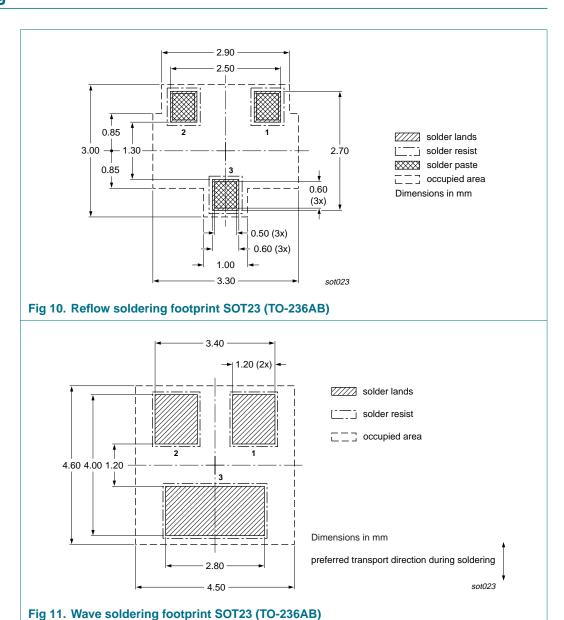
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing quantity		uantity
			3000	10000
PMBTA44	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA44_1	20080222	Product data sheet	-	-

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PMBTA44 **NXP Semiconductors**

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

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